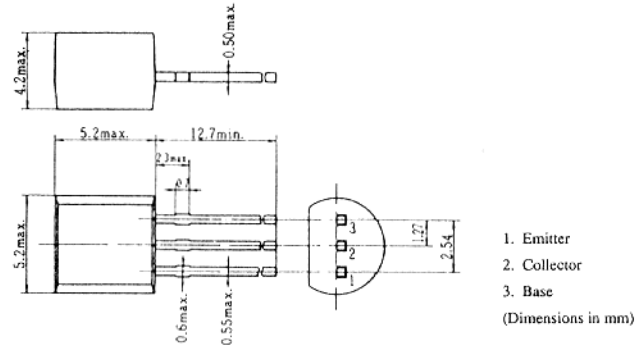


## 2SA1485

SILICON PNP EPITAXIAL  
LOW FREQUENCY AMPLIFIER

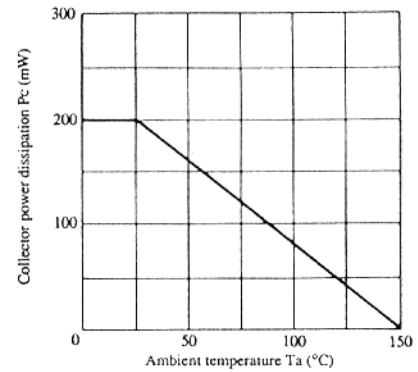


(JEDEC TO-92)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1485	Unit
Collector to base voltage	V <sub>CB0</sub>	-200	V
Collector to emitter voltage	V <sub>CE0</sub>	-200	V
Emitter to base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-100	mA
Collector power dissipation	P <sub>C*</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### ■ MAXIMUM COLLECTOR DISSIPATION CURVE

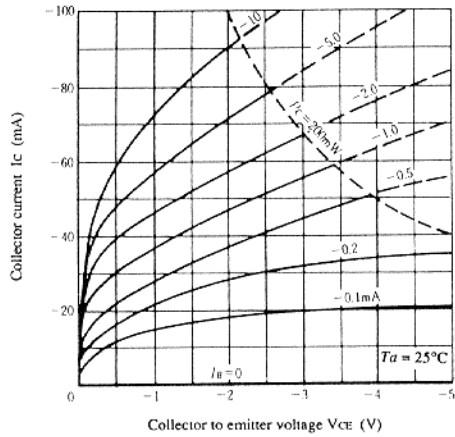


### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

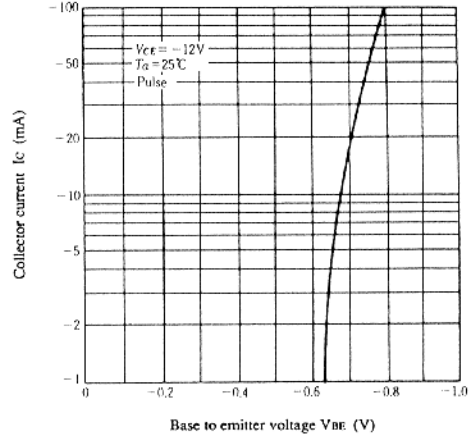
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0	-200	—	—	V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -0.5mA, R <sub>BE</sub> = ∞	-200	—	—	V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0	-5	—	—	V
Collector cutoff current	I <sub>CEO</sub>	V <sub>CE</sub> = -200V, R <sub>BE</sub> = ∞	—	—	-500	μA
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = -12V, I <sub>C</sub> = -2mA*	100	—	250	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -30mA, I <sub>B</sub> = -3mA*	—	—	-0.5	V
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -12V, I <sub>C</sub> = -2mA*	—	—	-1.0	V

\* Pulse Test

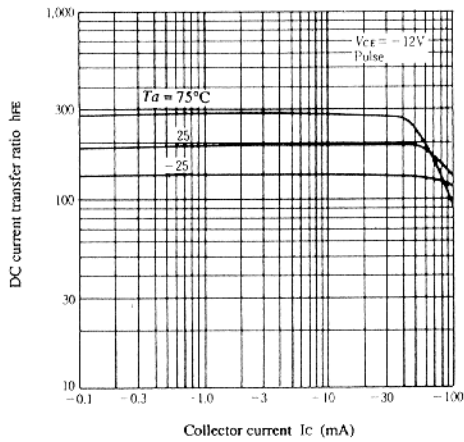
**TYPICAL OUTPUT CHARACTERISTICS**



**TYPICAL TRANSFER CHARACTERISTICS**



**DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT**



**COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT**

